

BUZ80A
BUZ80AFI

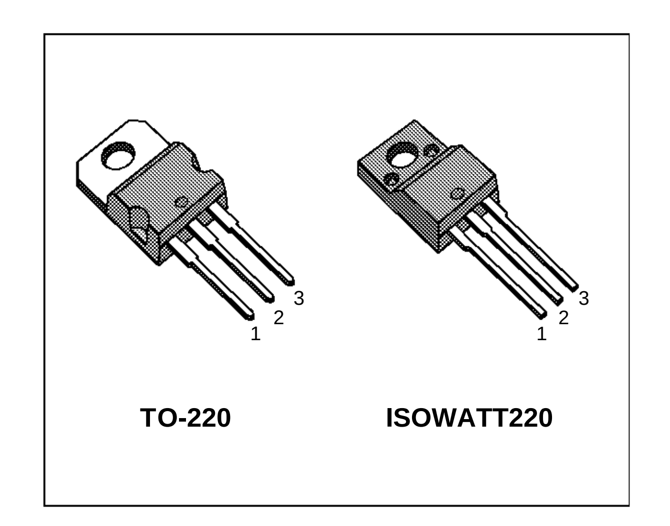
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTOR

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
BUZ80A	800 V	< 3 Ω	3.8 A
BUZ80AFI	800 V	< 3 Ω	2.4 A

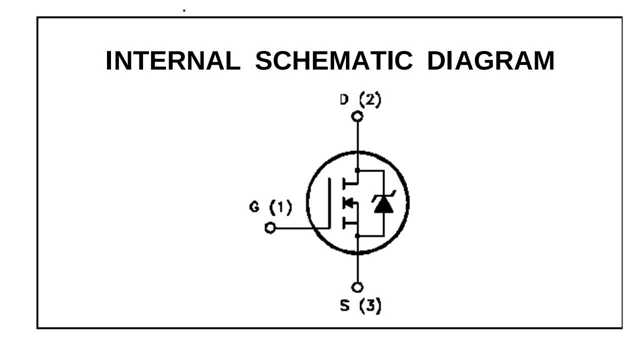
- TYPICAL $R_{DS(on)}$ = 2.5 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INPUT CAPACITANCE
- LOW GATE CHARGE
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING
- DC-AC INVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLY (UPS)



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BUZ80A	BUZ80AFI	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	800		V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	800		V
V_{GS}	Gate-source Voltage	± 20		V
I_D	Drain Current (continuous) at T_c = 25 °C	3.8	2.4	A
I_D	Drain Current (continuous) at T_c = 100 °C	2.3	1.4	A
I_{DM}(•)	Drain Current (pulsed)	15	15	A
P_{tot}	Total Dissipation at T_c = 25 °C	100	40	W
	Derating Factor	0.8	0.32	W/°C
V_{ISO}	Insulation Withstand Voltage (DC)	—	2000	V
T_{stg}	Storage Temperature	-65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

THERMAL DATA

		TO-220	ISOWATT220	
$R_{thj-case}$	Thermal Resistance Junction-case Max	1.25	3.12	$^oC/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient Max	62.5		$^oC/W$
$R_{thc-sink}$	Thermal Resistance Case-sink Typ	0.5		$^oC/W$
T_l	Maximum Lead Temperature For Soldering Purpose	300		^oC

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	3.8	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25\ ^oC$, $I_D = I_{AR}$, $V_{DD} = 50$ V)	200	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	8	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100\ ^oC$, pulse width limited by T_j max, $\delta < 1\%$)	2.2	A

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\ ^oC$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu A$ $V_{GS} = 0$	800			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	V_{DS} = Max Rating V_{DS} = Max Rating x 0.8 $T_c = 125\ ^oC$			250 1000	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20$ V			± 100	nA

ON (∗)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 1$ mA	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10$ V $I_D = 1.7$ A $V_{GS} = 10$ V $I_D = 1.7$ A $T_c = 100^oC$		2.5	3 6	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10$ V	3.8			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (∗)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 1.7$ A	1			S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25$ V $f = 1$ MHz $V_{GS} = 0$			1100 150 55	pF pF pF



ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 30 V I_D = 2.3 A R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 3)		65 150	90 200	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	V_{DD} = 600 V I_D = 3.8 A R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 5)		80	110	A/μs
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 400 V I_D = 5 A V_{GS} = 10 V		55 8 26	70	nC nC nC

SWITCHING OFF

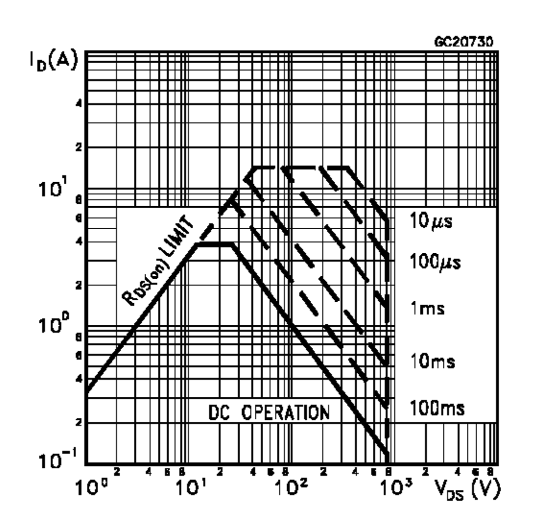
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 600 V I_D = 3.8 A R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 5)		110 140 150	145 190 200	ns ns ns

SOURCE DRAIN DIODE

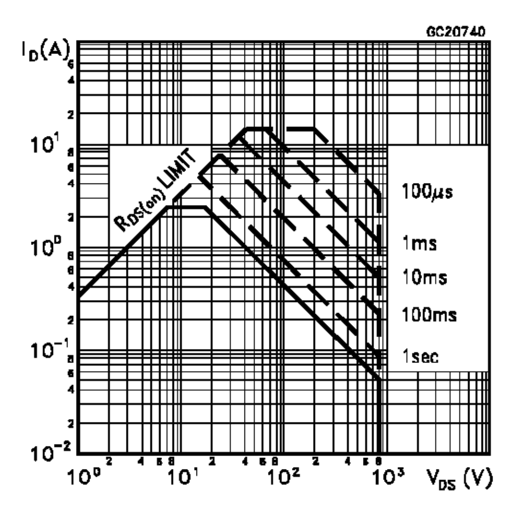
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				3.8 15	A A
V_{SD} (∗)	Forward On Voltage	I_{SD} = 7.6 A V_{GS} = 0			2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 3.8 A di/dt = 100 A/μs V_R = 100 V T_j = 150 °C (see test circuit, figure 5)		500 4.3 17		ns μC A

(∗) Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %
(•) Pulse width limited by safe operating area

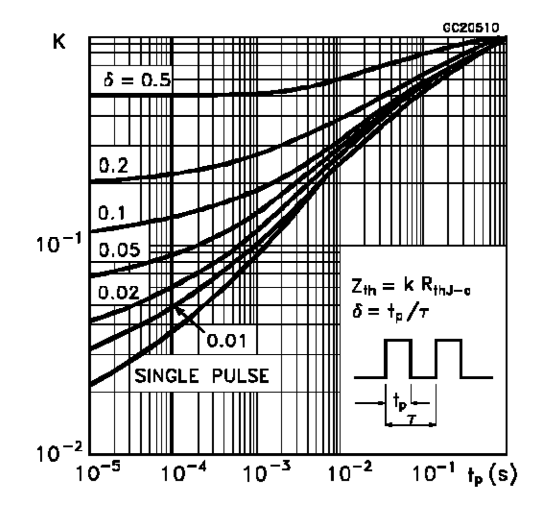
Safe Operating Areas For TO-220 Package



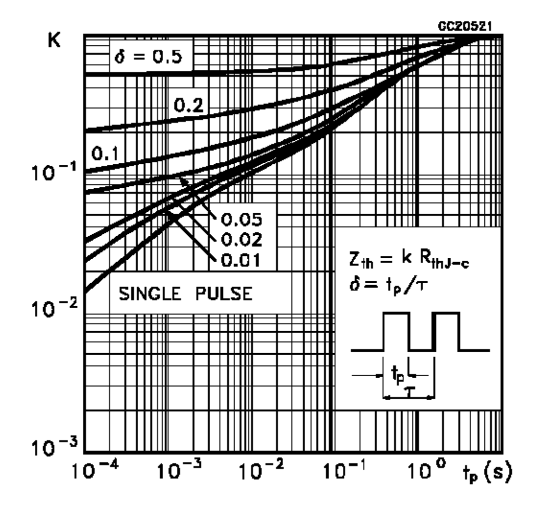
Safe Operating Areas For ISOWATT220 Package



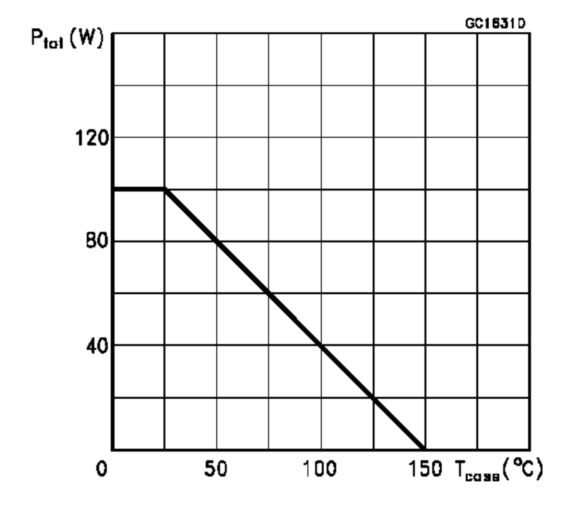
Thermal Impedeance For TO-220 Package



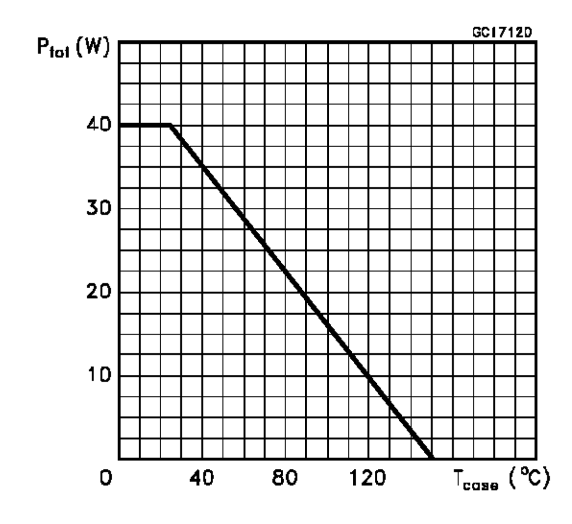
Thermal Impedance For ISOWATT220 Package



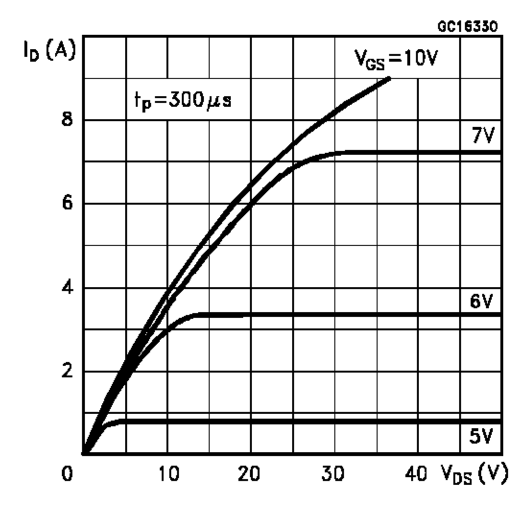
Derating Curve For TO-220 Package



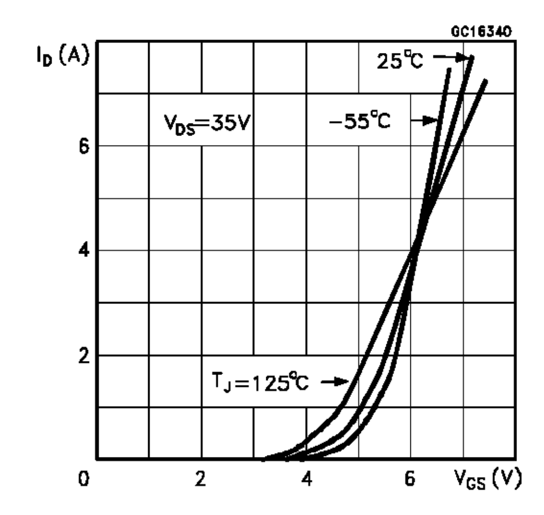
Derating Curve For ISOWATT220 Package



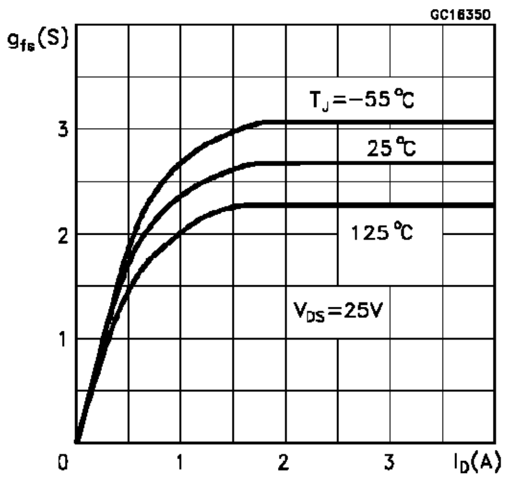
Output Characteristics



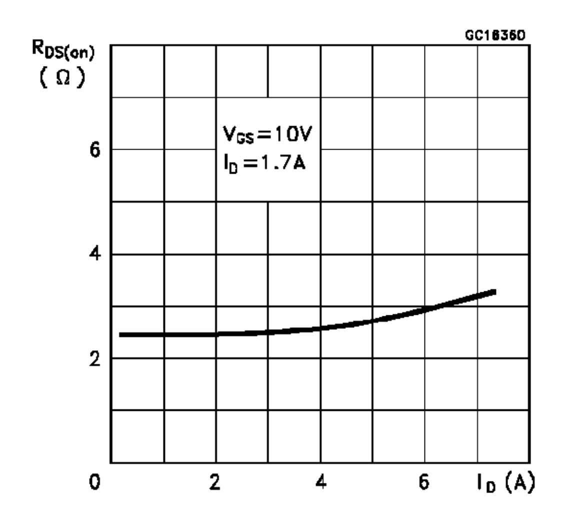
Transfer Characteristics



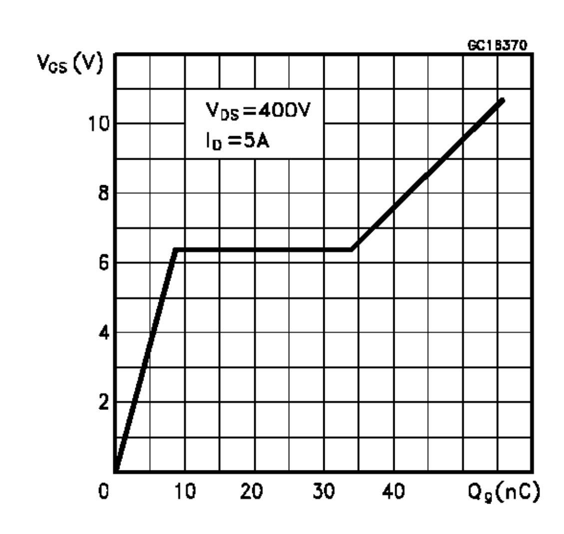
Transconductance



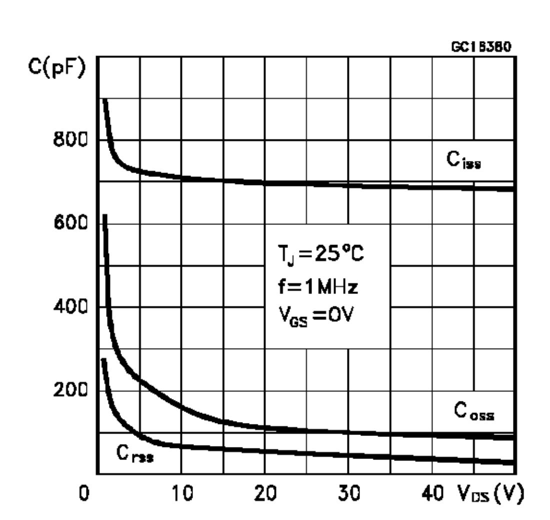
Static Drain-source On Resistance



Gate Charge vs Gate-source Voltage

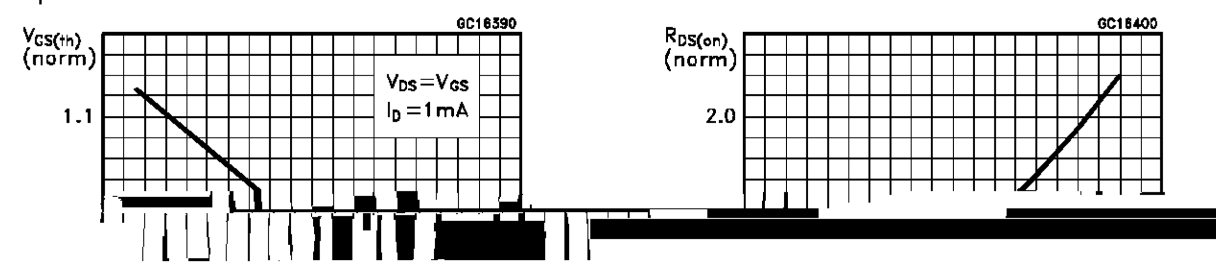


Capacitance Variations

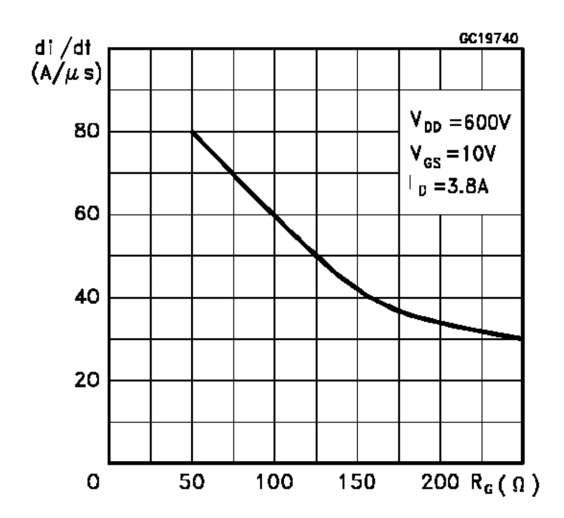


Normalized Gate Threshold Voltage vs Temperature

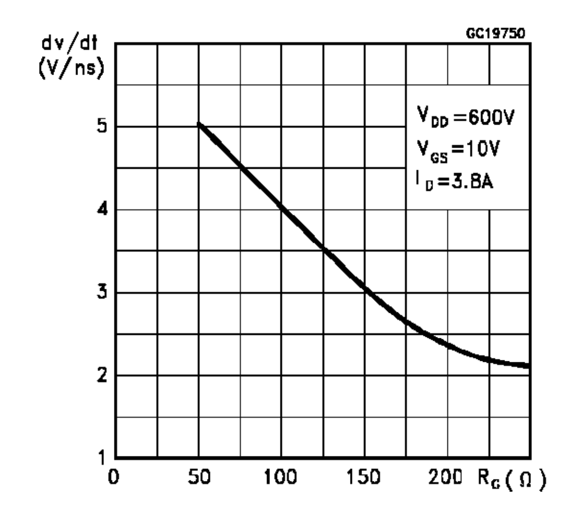
Normalized On Resistance vs Temperature



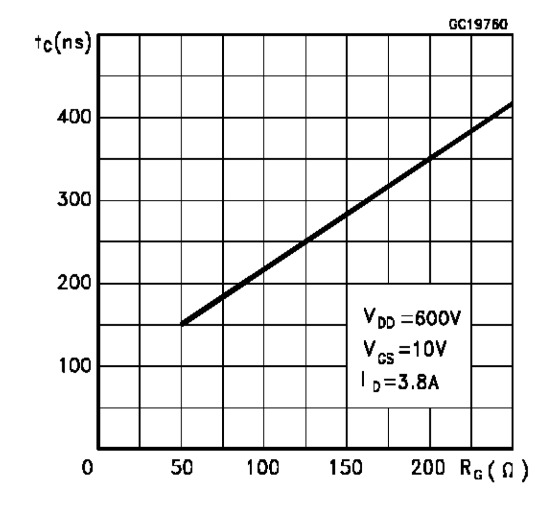
Turn-on Current Slope



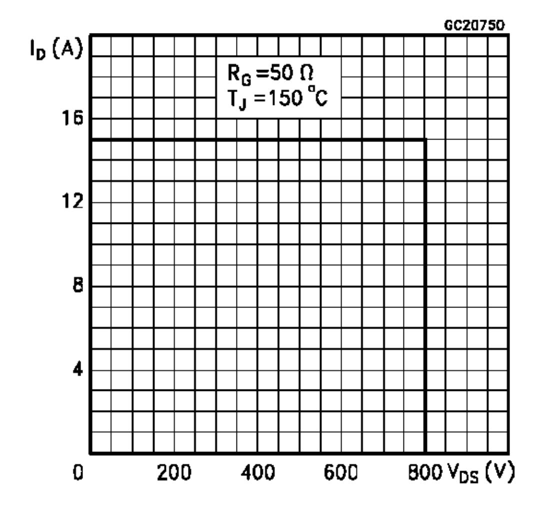
Turn-off Drain-source Voltage Slope



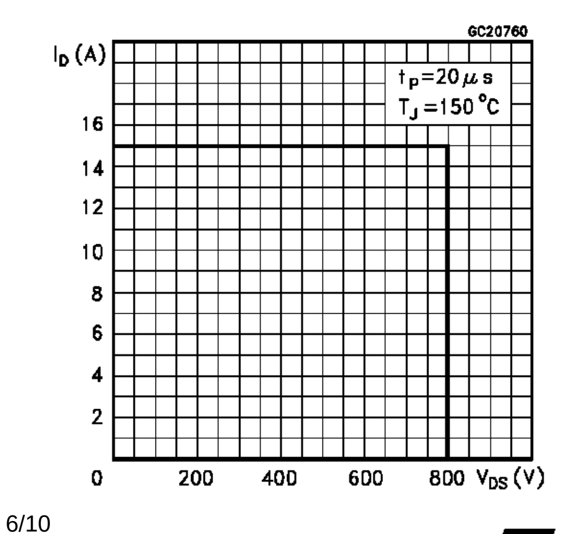
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

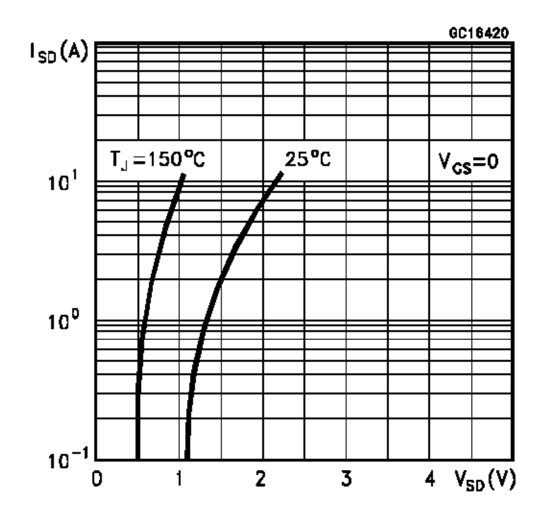


Fig. 1: Unclamped Inductive Load Test Circuits

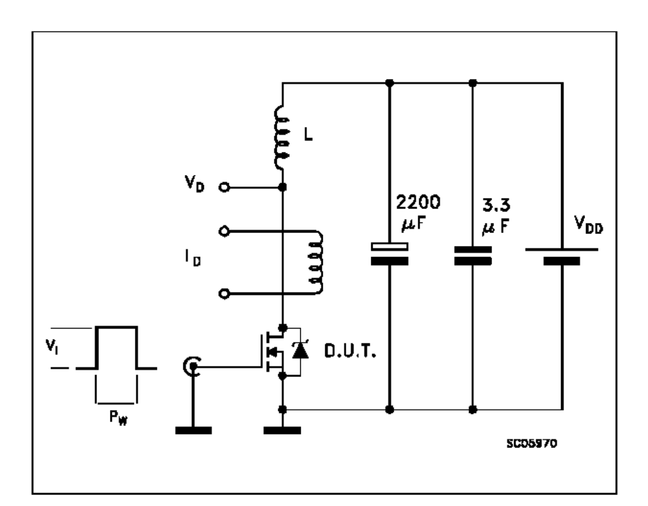


Fig. 2: Unclamped Inductive Waveforms

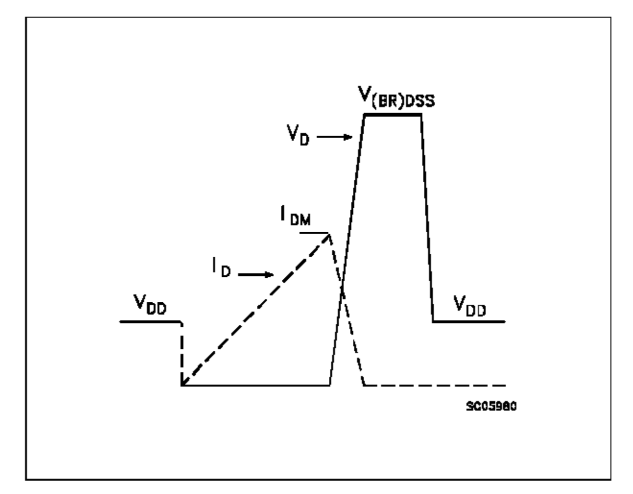


Fig. 3: Switching Times Test Circuits For Resistive Load

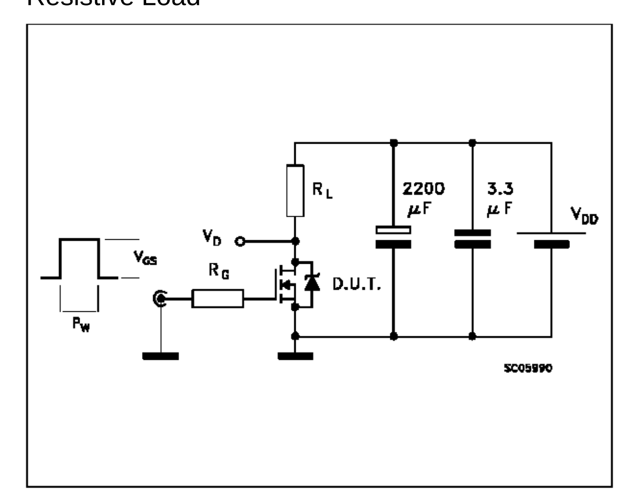


Fig. 4: Gate Charge Test Circuit

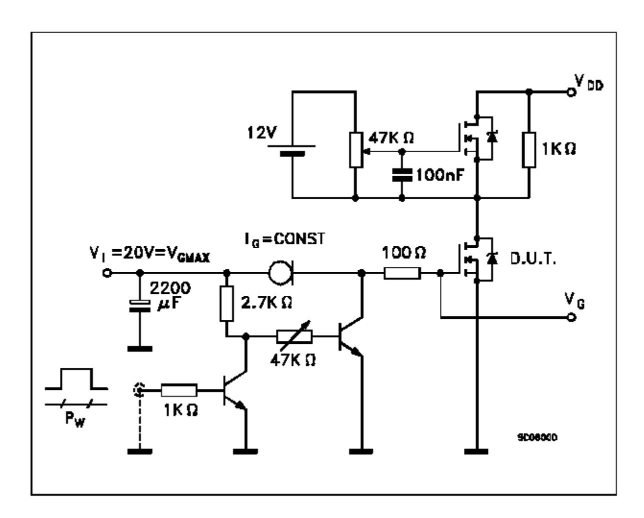
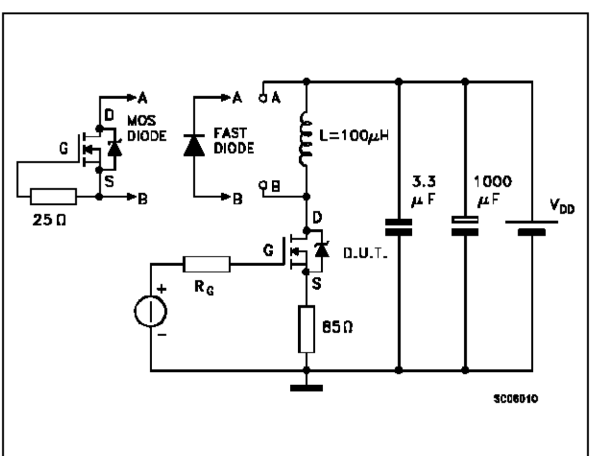
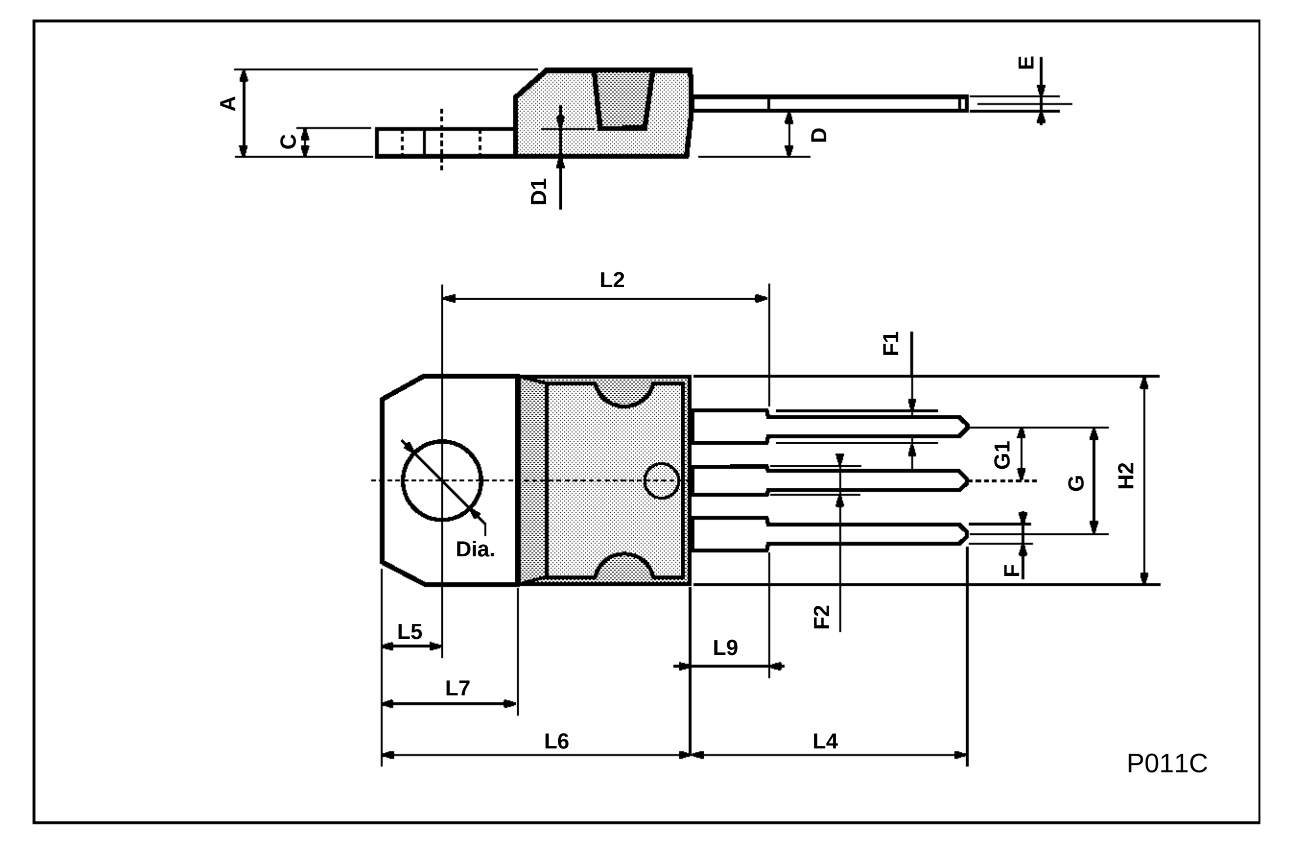


Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time



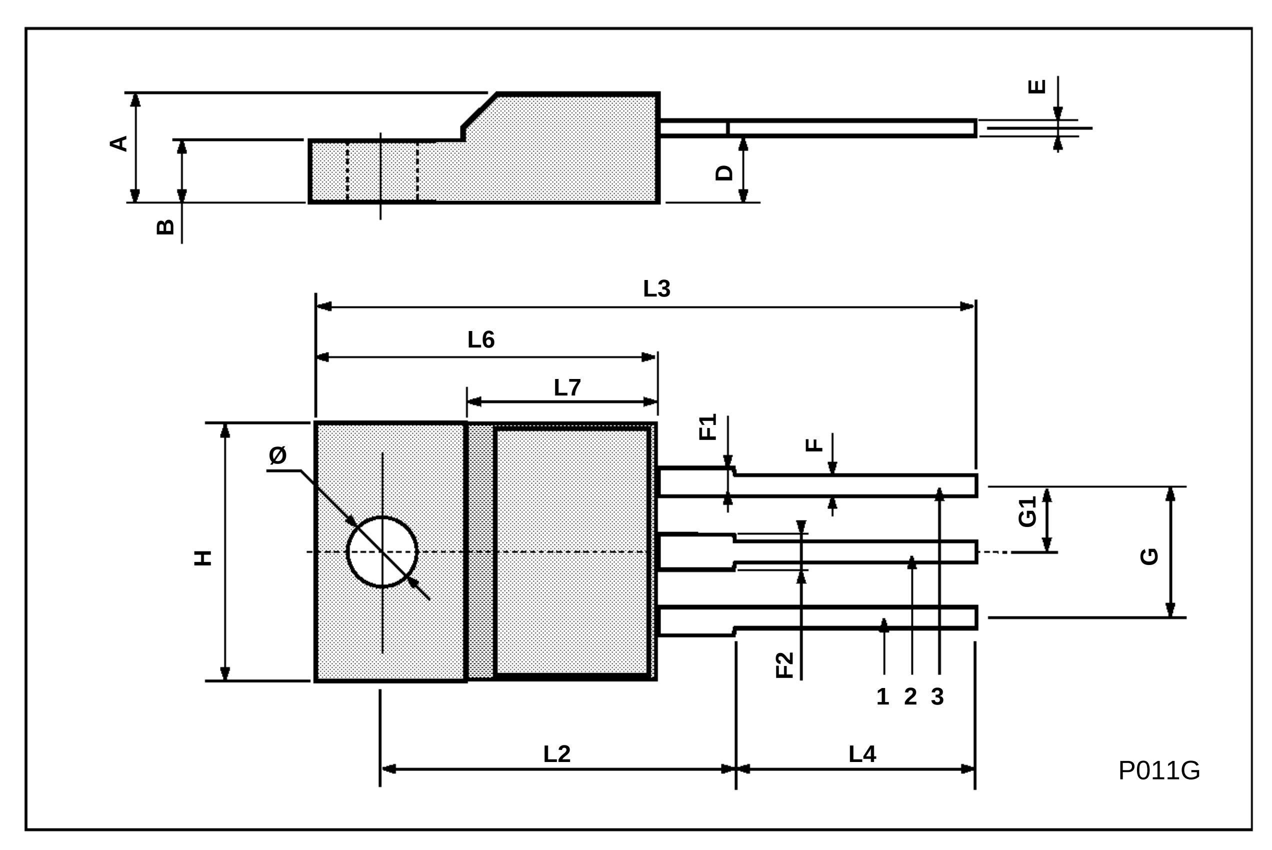
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



ISOWATT220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126




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